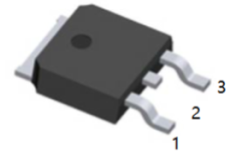


General Description

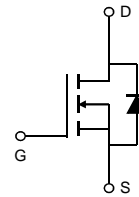
- Very Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications



1.G 2.D 3.S
TO-252(DPAK) top view

Application

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial
- $V_{DS}(V) = 100V$
- $I_D = 7A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 140m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 176m\Omega$ ($V_{GS} = 4.5V$)



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	7
		$T_C=100^\circ C$	5
Pulsed Drain Current ^C	I_{DM}	10	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ C$	3.5
		$T_A=70^\circ C$	3
Avalanche Current ^C	I_{AS}	3	A
Avalanche energy $L=0.1mH$ ^C	E_{AS}	0.5	mJ
V_{DS} Spike	10us	V_{SPIKE}	120
Power Dissipation ^B	P_D	$T_C=25^\circ C$	17
		$T_C=100^\circ C$	8.5
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ C$	5.0
		$T_A=70^\circ C$	3.2
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	$t \leq 10s$	20	$^\circ C/W$
Maximum Junction-to-Ambient ^{A,D}		Steady-State	40	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	7.3	8.8	$^\circ C/W$

Electrical Characteristics (T_J =25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.7	2.2	2.7	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5A		117	140	mΩ
		V _{GS} =4.5V, I _D =3A		140	176	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A		8.5		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.8	1.1	V
I _S	Maximum Body-Diode Continuous Current				7	A
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, f=1MHz		250	310	pF
C _{oss}	Output Capacitance			19	30	pF
C _{riss}	Reverse Transfer Capacitance			2.5	8	pF
R _g	Gate resistance	f=1MHz	5	10.5	16	Ω
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =5A		3.8	10	nC
Q _{g(4.5V)}	Total Gate Charge			1.8	6	nC
Q _{gs}	Gate Source Charge			0.8		nC
Q _{gd}	Gate Drain Charge			0.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =50V, R _L =10Ω, R _{GEN} =3Ω		5		ns
t _r	Turn-On Rise Time			3		ns
t _{D(off)}	Turn-Off DelayTime			19		ns
t _f	Turn-Off Fall Time			5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =5A, dI/dt=500A/μs		16		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =5A, dI/dt=500A/μs		52		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R_{θJA} t_s ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=175° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

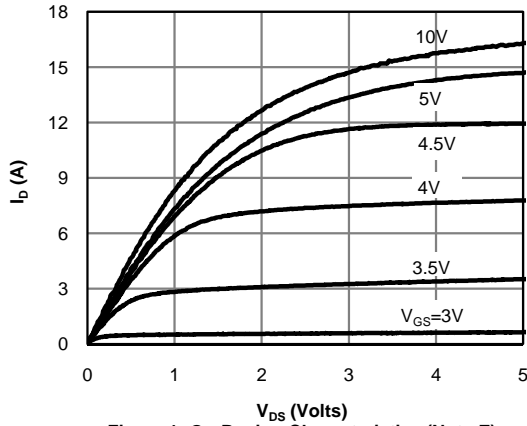


Figure 1: On-Region Characteristics (Note E)

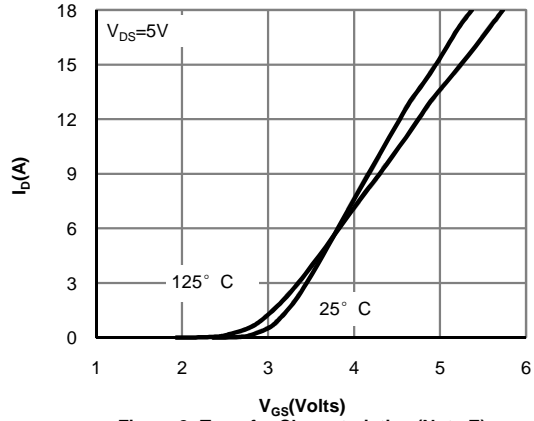


Figure 2: Transfer Characteristics (Note E)

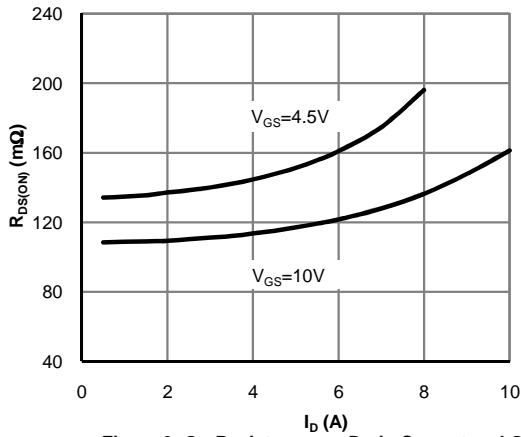


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

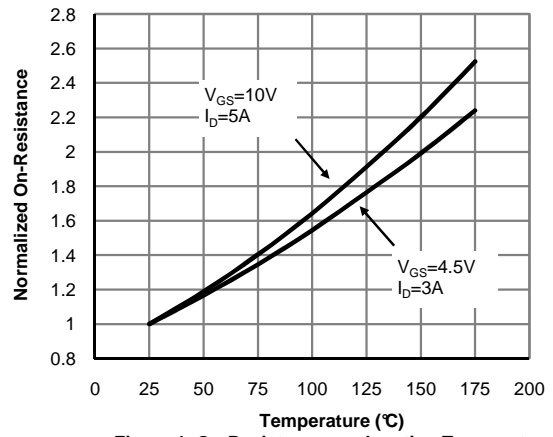


Figure 4: On-Resistance vs. Junction Temperature (Note E)

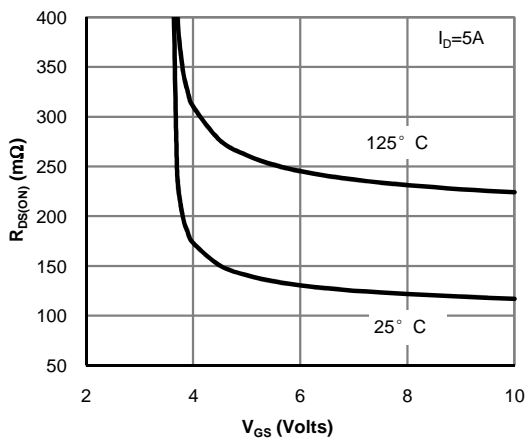


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

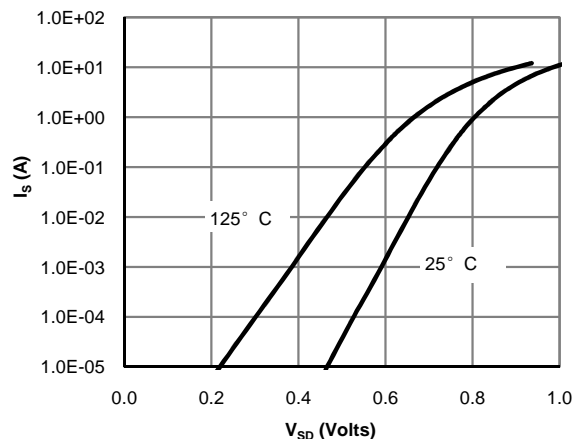


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

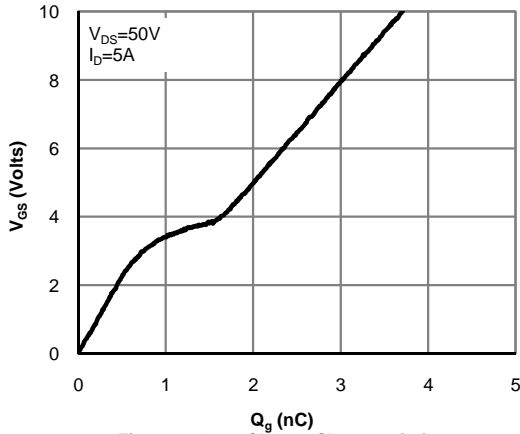


Figure 7: Gate-Charge Characteristics

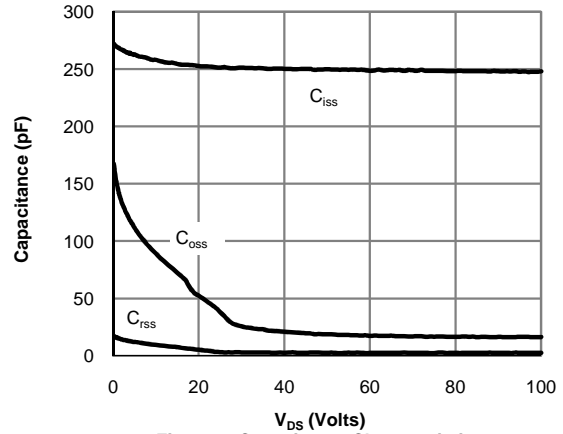


Figure 8: Capacitance Characteristics

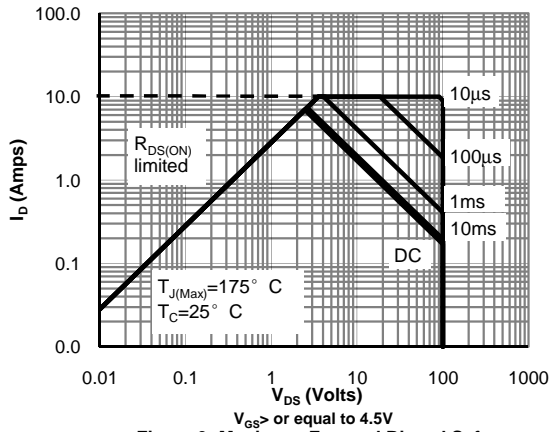


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

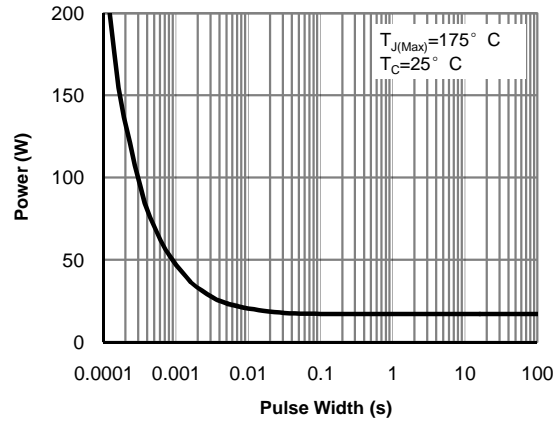


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

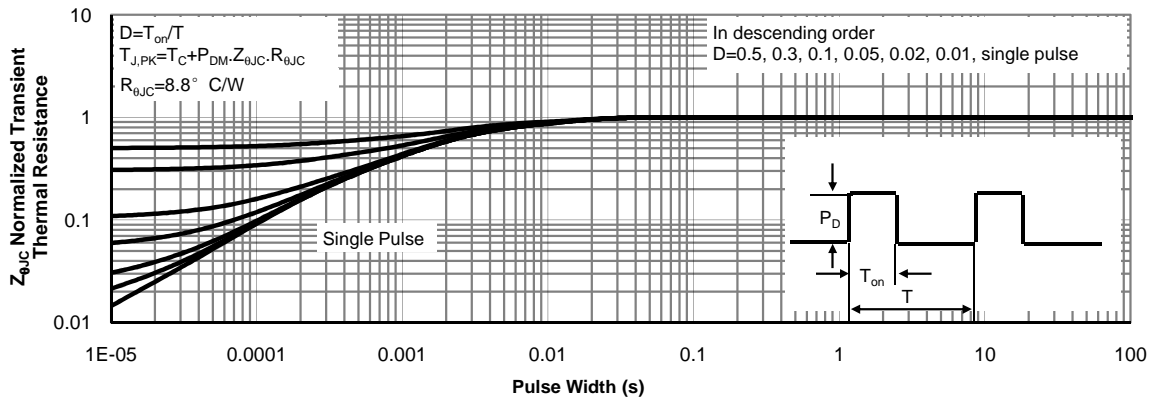


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

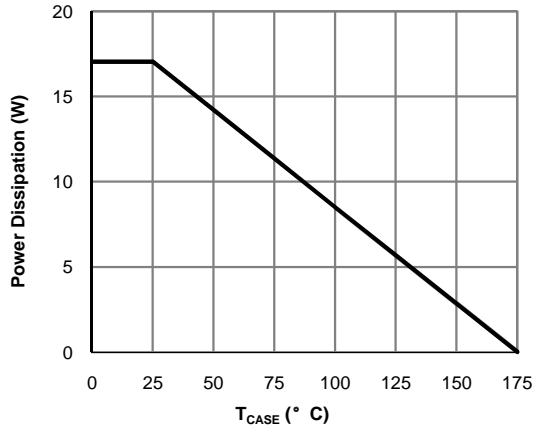


Figure 12: Power De-rating (Note F)

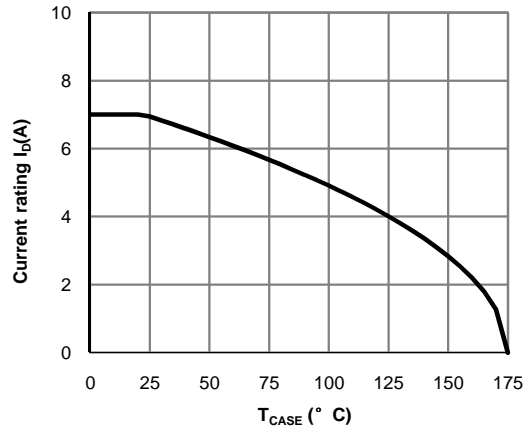


Figure 13: Current De-rating (Note F)

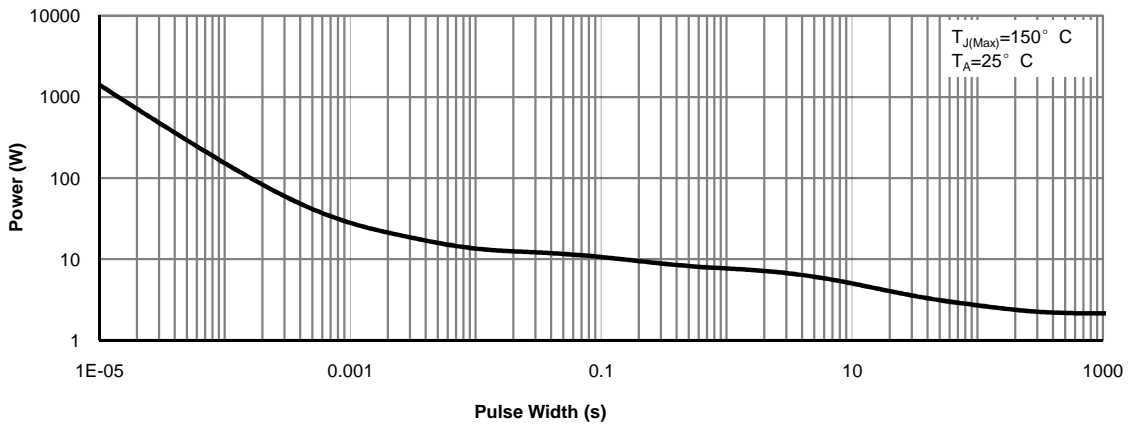


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

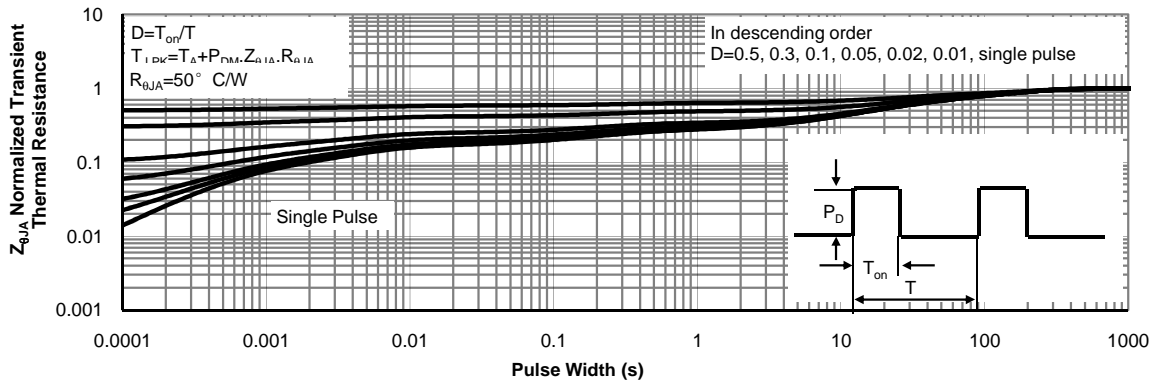
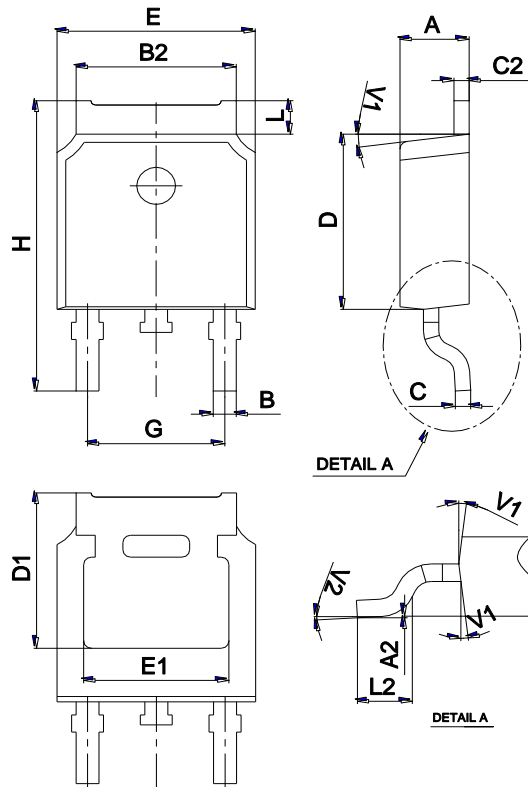


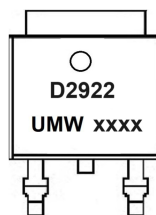
Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW AOD2922	TO-252	2500	Tape and reel

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[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1_T0_00201](#) [PJMF380N65E1_T0_00201](#)
[PJMF280N60E1_T0_00201](#) [PJMF600N65E1_T0_00201](#) [PJMF900N65E1_T0_00201](#)